



DMT35M4LFDF4

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
201/	9mΩ @ V <sub>GS</sub> = 10V	12A
30V	13.5mΩ @ V <sub>GS</sub> = 4.5V	10A

# Description

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# Applications

- General Purpose Interfacing Switch
- **Power Management Functions**

X2-DFN2020-6 (Type W)

Pin

Top View

Bottom View

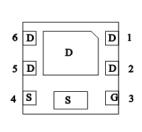
# **30V N-CHANNEL ENHANCEMENT MODE MOSFET**

#### Features

- 0.4mm Profile—Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

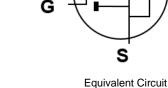
# **Mechanical Data**

- Case: X2-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.006 grams (Approximate)



Pin Out

**Bottom View** 



D

S

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT35M4LFDF4-7	X2-DFN2020-6 (Type W)	3,000/Tape & Reel
DMT35M4LFDF4-13	X2-DFN2020-6 (Type W)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

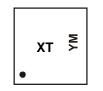
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**

Site 1



XT = Product Type Marking Code YM = Date Code Marking Y = Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н		J	K	L	М	Ν	0	Р	R	S	Т
									1	1	1	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



XT = Product Type Marking Code YWX = Date Code Marking

Y = Year (ex: 1 = 2021) W = Week (ex: a = Week 27; z Represents Week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	0	1	2	3	4	5	6	7	8	9	0	1
Week		1-26 27-52 53						27-52				
Code		A	N-Z		a-z			Z				
Internal Code	Su	un	Mor	า	Tue	1	Wed	Thu		Fri		Sat
Code		Г	U		V		W	Х		Y		7



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage		VDSS	30	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current Man (0)/ (Nata C)	T <sub>A</sub> = +25°C	1-	12	٨	
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	T <sub>A</sub> = +70°C	ID	10	A	
Maximum Body Diode Forward Current		ls	3	A	
Pulsed Drain Current (380µs Pulse, Duty Cycle = 19	%)		IDM	80	A
Pulsed Drain Body Diode Forward Current (380µs F	Pulse, Duty Cycle	e = 1%)	lsм	80	A
Avalanche Current (L = 0.1mH) (Note 8)		I <sub>AS</sub>	22	A	
Avalanche Energy (L = 0.1mH) (Note 8)			Eas	25	mJ

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.91	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	138	°C/W
Total Power Dissipation (Note 6)		PD	2.19	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	57	°C/W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	9.6	C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						-
Drain-Source Breakdown Voltage	BVDSS	30	—	_	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$
Gate-Source Leakage	lgss	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.15	—	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
Static Drain-Source On-Resistance	Proven		6	9	mΩ	VGS = 10V, ID = 20A
	R <sub>DS(ON)</sub>	_	8	13.5	11152	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 15A
Diode Forward Voltage	Vsd		0.7	1	V	$V_{GS} = 0V$ , $I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	Ciss		1009			V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	Coss	_	925	_	pF	
Reverse Transfer Capacitance	Crss	—	50	_		1 = 1.00012
Gate Resistance	Rg	_	2	_	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	8.1	—		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	14.9	_	nC	
Gate-Source Charge	Qgs	—	2.3	_	nc	Vdd = 15V, Id = 9A
Gate-Drain Charge	Q <sub>gd</sub>	_	3.4	_		
Turn-On Delay Time	td(on)	_	3.6	_		
Turn-On Rise Time	t <sub>R</sub>	_	4.4			$V_{DD} = 15V, V_{GS} = 10V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	15	_	ns	$R_g = 3\Omega$ , $I_D = 9A$
Turn-Off Fall Time	tF	_	6.9			
Reverse Recovery Time	t <sub>RR</sub>	_	29.4		ns	
Reverse Recovery Charge	Qrr	_	19.2		nC	I <sub>F</sub> = 1.5A, di/dt = 100A/µs

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

bevice mounted on FR-4 substrate PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).

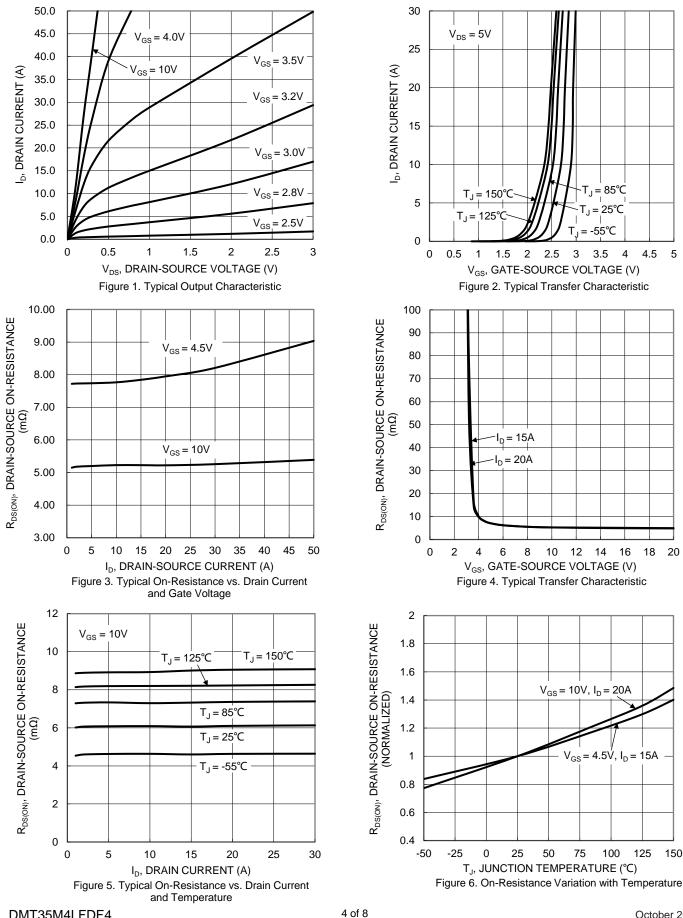
8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

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DMT35M4LFDF4 Datasheet number: DS43222 Rev. 3 - 2

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 $I_D = 1mA$ 

125

 $\mathbf{C}_{\text{iss}}$ 

 $\mathbf{C}_{\mathrm{oss}}$ 

 $\mathbf{C}_{\mathrm{rss}}$ 

25

30

150

100

 $I_{\rm D} = 250 \mu A$ 

25

10

. P<sub>w</sub>

1ms P<sub>W</sub> = 10ms

Ρ

15

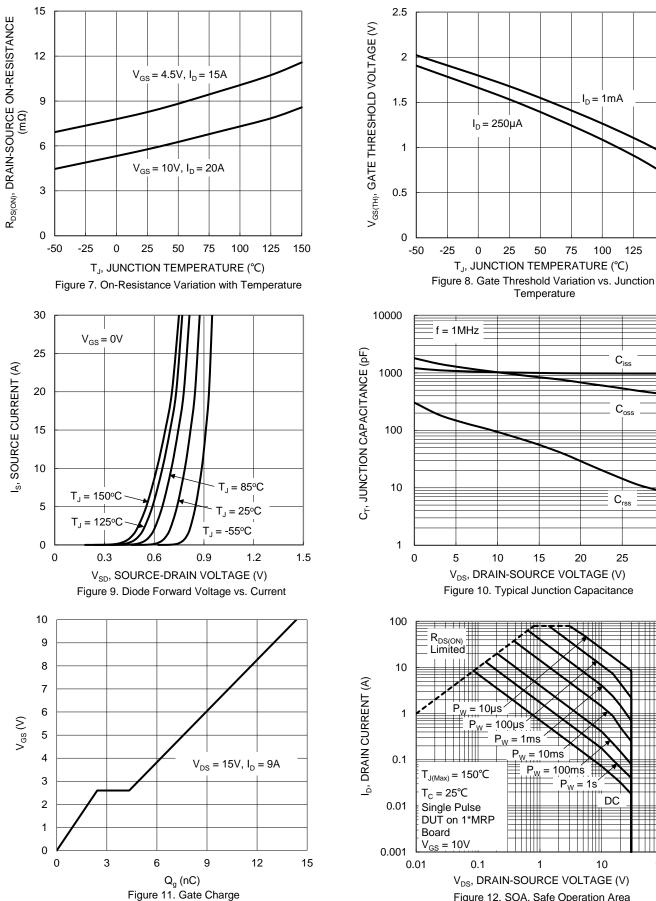
20

0

50

Temperature

75



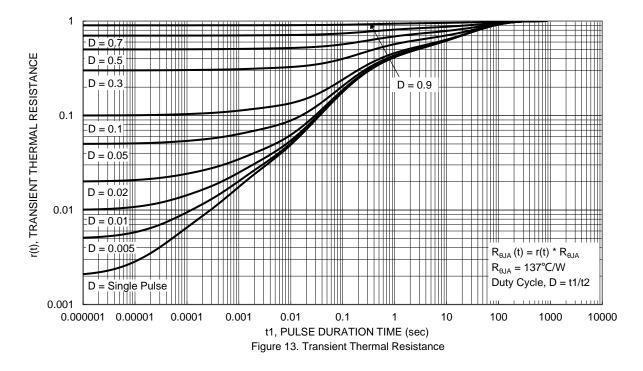
DC DUT on 1\*MRP 0.1 10 1 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

= 100mś

Р = 1s

DMT35M4LFDF4 Datasheet number: DS43222 Rev. 3 - 2 100

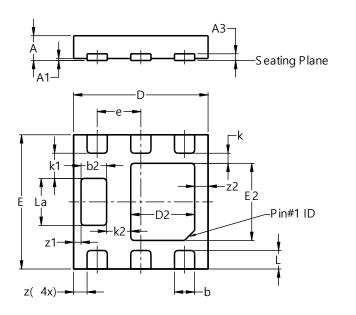






# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

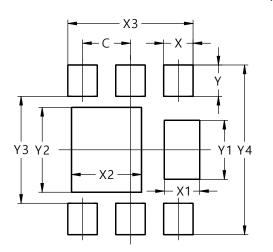


X2-DFN2020-6 (Type W)
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	X2-DFN Typ		
Dim	Min	Max	Тур
Α	0.34	0.40	0.37
A1	0.00	0.05	0.02
A3			0.100
b	0.25	0.35	0.30
b2	0.33	0.43	0.38
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
е			0.65
k			0.15
k1			0.375
k2			0.36
L	0.225	0.325	0.275
La	0.65	0.75	0.70
Z	_		0.20
z1			0.11
z2			0.20
All	Dimensi	ions in r	nm

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



## X2-DFN2020-6 (Type W)

Dimensions	Value (in mm)		
С	0.650		
X	0.400		
X1	0.480		
X2	0.950		
X3	1.700		
Y	0.425		
Y1	0.800		
Y2	1.150		
Y3	1.450		
Y4	2.300		



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